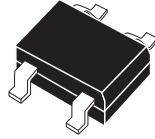


CBR1U-D010S  
CBR1U-D020S

**SURFACE MOUNT  
1.0 AMP ULTRA FAST  
SILICON BRIDGE RECTIFIER**



**SMDIP CASE**

**Central**<sup>TM</sup>  
**Semiconductor Corp.**

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CBR1U-D010S, CBR1U-D020S types are silicon full wave ultra fast bridge rectifier mounted in a durable epoxy surface mount molded case, utilizing glass passivated chips.

**MARKING CODE: FULL PART NUMBER**

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

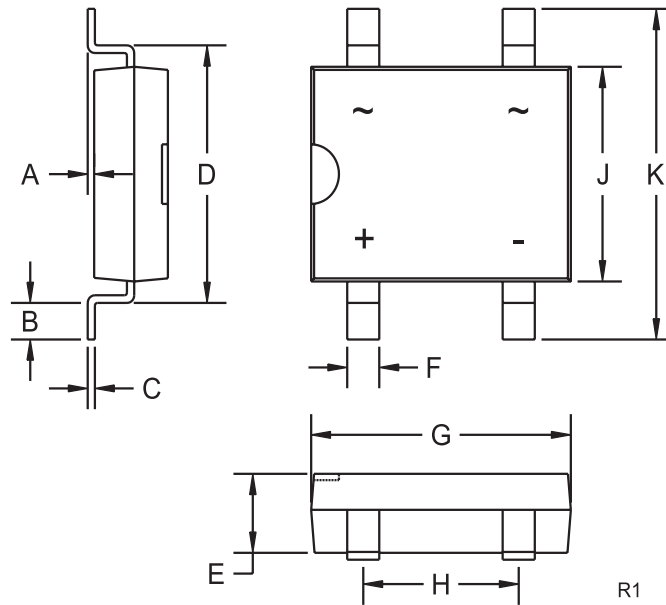
	<b>SYMBOL</b>	<b>CBR1U-D010S</b>	<b>CBR1U-D020S</b>	<b>UNITS</b>
Peak Repetitive Reverse Voltage	$V_{RRM}$	100	200	V
DC Blocking Voltage	$V_R$	100	200	V
RMS Reverse Voltage	$V_{R(RMS)}$	70	140	V
Average Forward Current ( $T_A=40^\circ\text{C}$ )	$I_O$		1.0	A
Peak Forward Surge Current	$I_{FSM}$		50	A
Operating and Storage Junction Temperature	$T_J, T_{stg}$		-65 to +150	$^\circ\text{C}$
Thermal Resistance	$\Theta_{JA}$		40	$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

<b>SYMBOL</b>	<b>TEST CONDITIONS</b>	<b>MIN</b>	<b>MAX</b>	<b>UNITS</b>
$V_F$	$I_F=1.0\text{A}$ (Per Diode)		1.05	V
$I_R$	$V_R=\text{Rated } V_{RRM}$		5.0	$\mu\text{A}$
$I_R$	$V_R=\text{Rated } V_{RRM}; T_A=125^\circ\text{C}$		1.0	mA
$t_{rr}$	$I_F=500\text{mA}, I_R=1.0\text{A}, I_{rr}=250\text{mA}$		50	ns

R2 (13-November 2002)

**SMDIP CASE - MECHANICAL OUTLINE**



**MARKING CODE:  
FULL PART NUMBER**

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.008	0.10	0.20
B	0.040	0.060	1.02	1.52
C	0.009		0.23	
D	0.290	0.310	7.37	7.87
E	0.086	0.098	2.18	2.49
F	0.038	0.042	0.97	1.07
G	0.316	0.335	8.03	8.51
H	0.195	0.205	4.95	5.21
J	0.245	0.255	6.22	6.48
K	0.360	0.410	9.14	10.41

SMDIP (REV: R1)

R2 (13-November 2002)